MSKSEMI















ESD

TVS

TSS

MOV

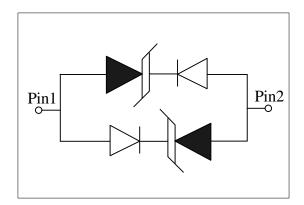
GDT

PLED

Broduct data sheet



Schematic & PIN Configuration





SOD-523

Features

- Small Body Outline Dimensions
- Low Body Height: 0.024" (0.6 mm) nom
- Bidirectional ESD protection of one I/O line
- Low clamping voltage
- Working voltage: 5V
- Low leakage current
- Solid-state silicon-avalanche technology

IEC COMPATIBILITY (EN61000-4)

- IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)

Mechanical Characteristics

- JEDEC SOD-523 package
- Marking : Marking Code
- Packaging : Tape and Reel per EIA 481
- RoHS Compliant

Applications

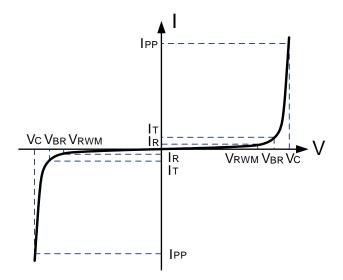
- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras
- MP3 players

| Absolute Maximum Rating | | | | |
|-------------------------|--------|--------------|-------|--|
| Rating | Symbol | Value | Units | |
| Operating Temperature | TJ | -55 to + 125 | °C | |
| Storage Temperature | Тѕтс | -55 to +150 | °C | |



Electrical Parameters (T=25°C)

| Symbol | Parameter |
|-----------------|--------------------------------|
| Ірр | Reverse Peak Pulse Current |
| Vc | Clamping Voltage @ IPP |
| VRWM | Reverse Stand-Off Voltage |
| lR | Reverse Leakage Current @ VRWM |
| V _{BR} | Breakdown Voltage @ IT |
| lτ | Test Current |



Electrical Characteristics

| MS05D5UC-B | | | | | | |
|-----------------------------------|------------------|--|---------|---------|---------|-------|
| Parameter | Symbol | Conditions | Minimum | Typical | Maximum | Units |
| Reverse Stand-Off Voltage | V_{RWM} | | | | 5.0 | V |
| Reverse Breakdown Voltage | V_{BR} | I _T =1mA | 6.0 | | 10.0 | V |
| Reverse Leakage Current | I _R | V _{RWM} =5V, T=25°C | | | 200 | nA |
| ESD Clamping Voltage ¹ | Vc | $I_{PP} = 4A$ $t_{p} = 0.2/100$ ns | | 11.9 | | V |
| ESD Clamping Voltage ¹ | Vc | $I_{PP} = 16A$ $t_{p} = 0.2/100$ ns | | 23.4 | | V |
| Dynamic Resistance ^{1,2} | R _{DYN} | TLP=0.2/100ns | | 0.95 | | Ω |
| Junction Capacitance | Cj | V _R =0V, f=1MHz | | 0.5 | 1.0 | pF |

Notes: 1, TLP Setting: t_p =100ns, t_r =0.2ns, I_{TLP} and V_{TLP} sample window: t_1 =70ns to t_2 =90ns.

2. Dynamic resistance calculated from IPP=4A to IPP=16A using "Best Fit".



Typical Characteristics

Figure 1: Normalized Junction Capacitance vs. Reverse Voltage

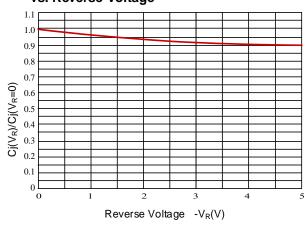


Figure 2: Power Derating Curve

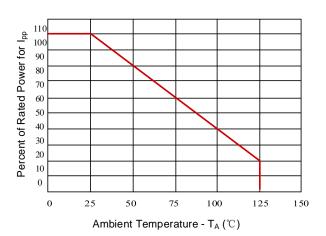


Figure 3: TLP Positive I-V Curve

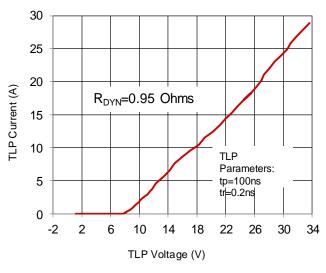
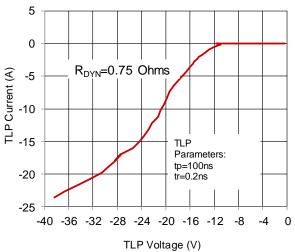
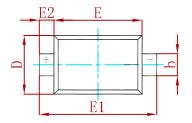


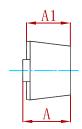
Figure 4: TLP Negative I-V Curve

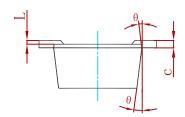




PACKAGE MECHANICAL DATA

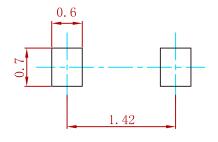






| Cumbal | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| Symbol | Min | Max | Min | Max |
| Α | 0.510 | 0.770 | 0.020 | 0.031 |
| A1 | 0.500 | 0.700 | 0.020 | 0.028 |
| b | 0.250 | 0.350 | 0.010 | 0.014 |
| С | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 0.750 | 0.850 | 0.030 | 0.033 |
| E | 1.100 | 1.300 | 0.043 | 0.051 |
| E1 | 1.500 | 1.700 | 0.059 | 0.067 |
| E2 | 0.200 REF | | 0.008 | B REF |
| L | 0.010 | 0.070 | 0.001 | 0.003 |
| θ | 7° RFF | | 7° I | RFF |

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|------------|---------|------|
| MS05D5UC-B | SOD-523 | 3000 |



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